

Supplementary Information

Structural, Electronic and Optical Properties of four α -Se-based Heterostructures with Hyperbolic Characteristics

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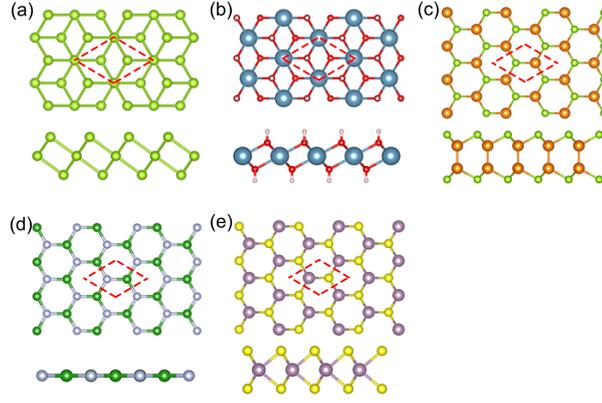


Figure S 1: (Color online). (a)-(e) Optimized structure of α -Se, $\text{Ca}(\text{OH})_2$, GaSe, h-BN and MoS_2 monolayers, respectively.

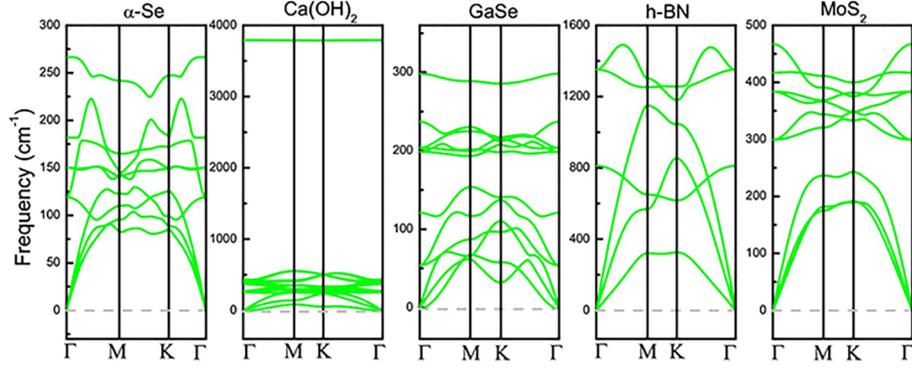


Figure S 2: (Color online). (a)-(e) The calculated phonon dispersion curves of α -Se, $\text{Ca}(\text{OH})_2$, GaSe, h-BN and MoS_2 monolayers, respectively.

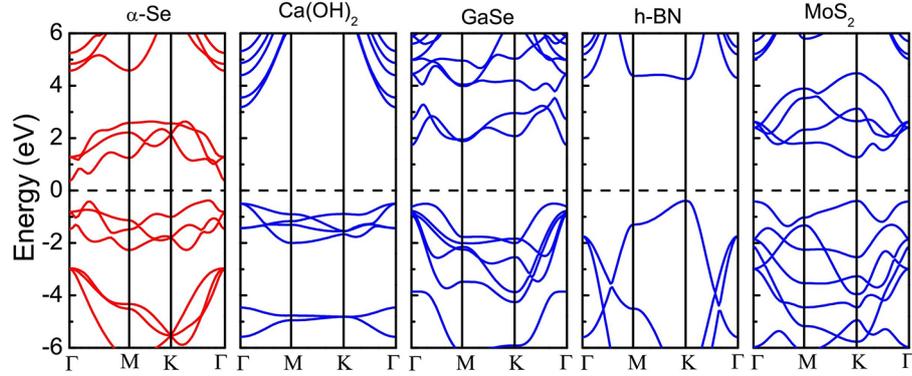


Figure S 3: (Color online). (a)-(e) The calculated electronic band structures of α -Se, $\text{Ca}(\text{OH})_2$, GaSe, h-BN and MoS_2 monolayers with PBE method, respectively.

Table S I: The calculated lattice constants (\AA), band gap (eV) and band gap type of α -Se, $\text{Ca}(\text{OH})_2$, GaSe, h-BN and MoS_2 monolayers, respectively

structure	α -Se	$\text{Ca}(\text{OH})_2$	GaSe	h-BN	MoS_2
Lattice (\AA)	3.72	3.62	3.82	2.51	3.18
E_g (eV)	0.73	3.68	2.23	4.65	1.68
Band gap type	Indirect	Direct	Indirect	Direct	Direct

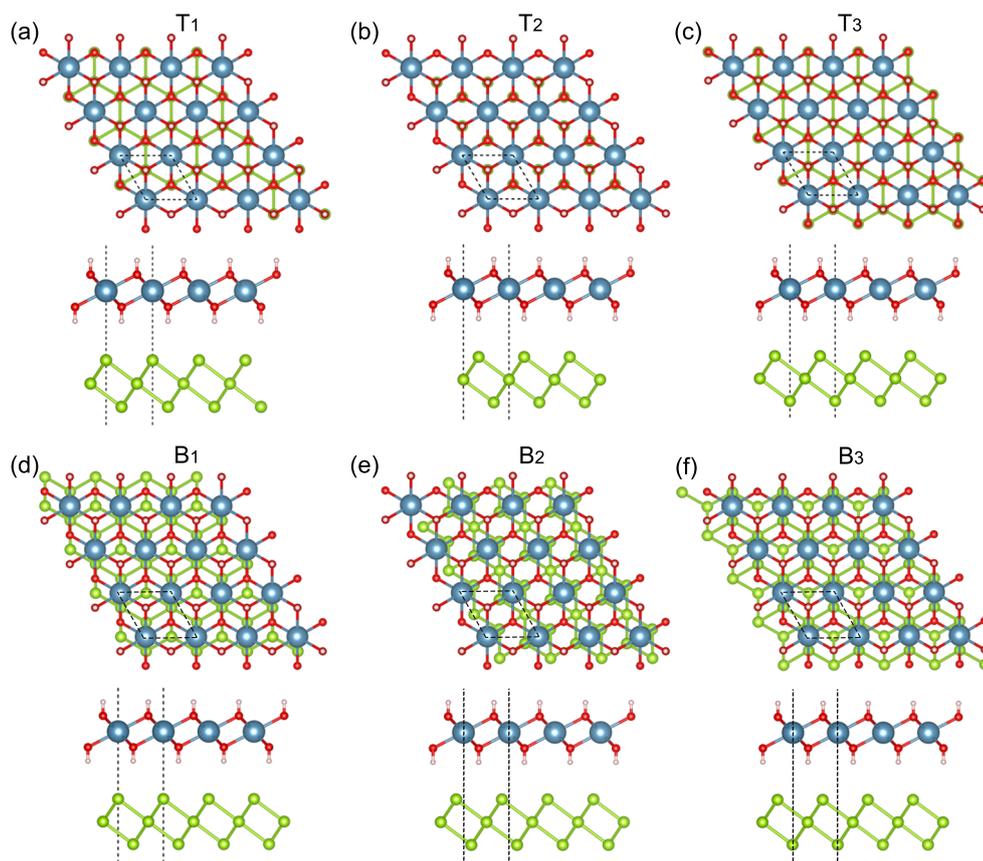


Figure S 4: (Color online). Top and side views of α -Se/Ca(OH)₂ heterobilayer with six types of stacking configurations: (a) T₁, (b) T₂, (c) T₃, (d) B₁, (e) B₂ and (f) B₃. The black dashed lines represent the unit cell.

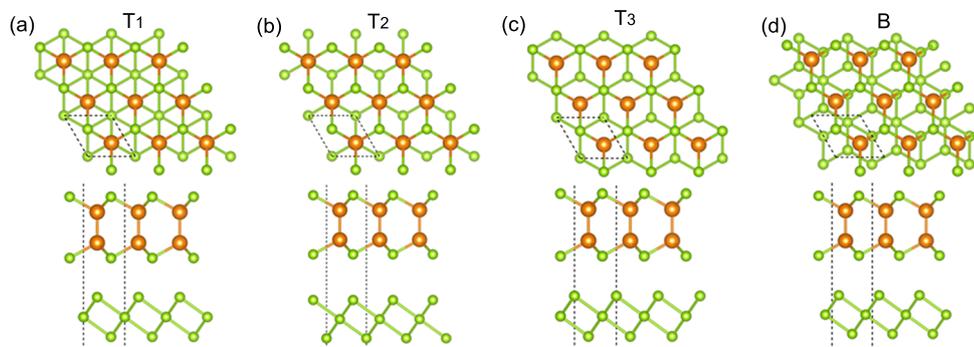


Figure S 5: (Color online). Top and side views of α -Se/GaSe heterobilayer with four types of stacking configurations: (a) T₁, (b) T₂, (c) T₃ and (d) B. The black dashed lines represent the unit cell.

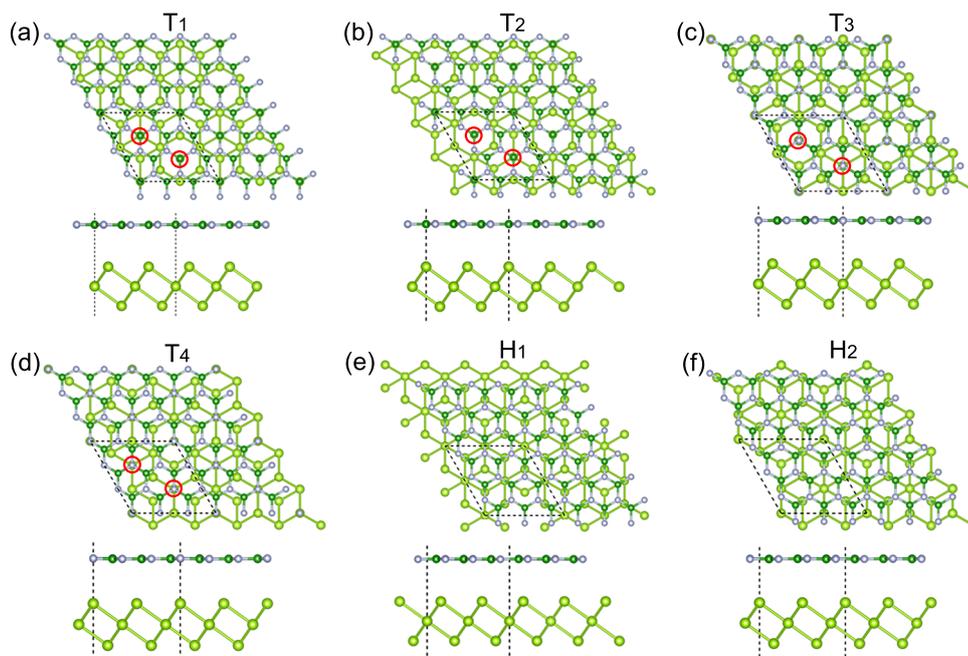


Figure S 6: (Color online). Top and side views of α -Se/h-BN heterobilayer with four types of stacking configurations: (a) T₁, (b) T₂, (c) T₃, (d) T₄, (e) H₁ and (f) H₂. The black dashed lines represent the unit cell.

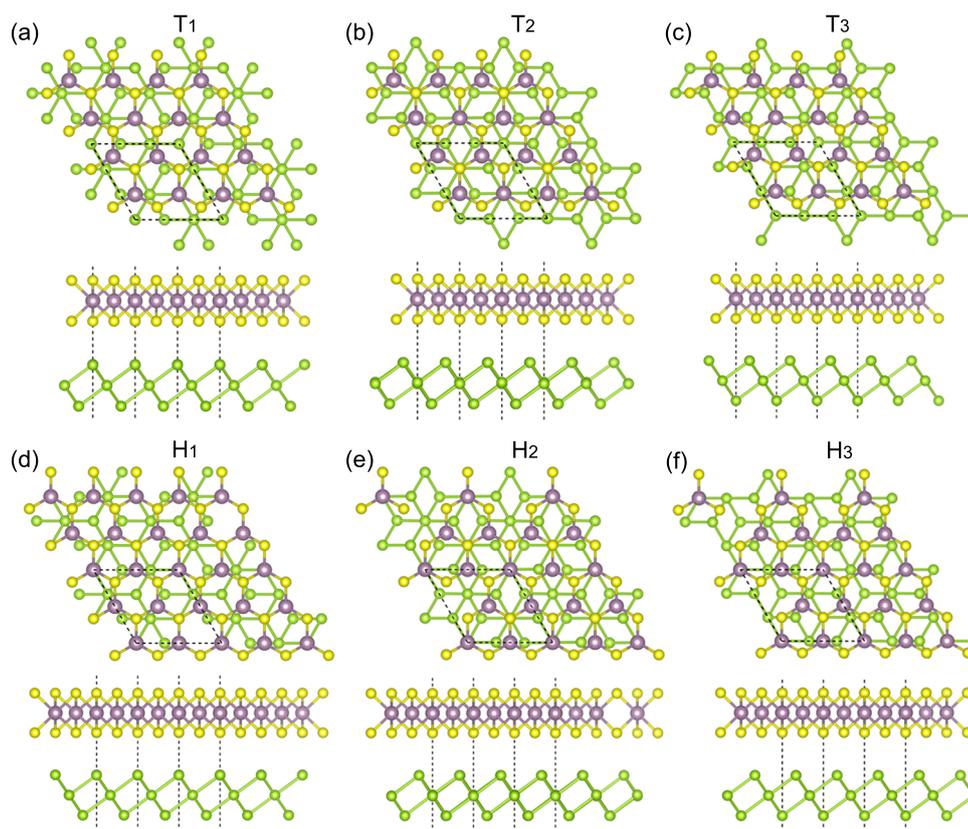


Figure S 7: (Color online). Top and side views of α -Se/MoS₂ heterobilayer with four types of stacking configurations: (a) T₁, (b) T₂, (c) T₃, (d) H₁, (e) H₂ and (f) H₃. The black dashed lines represent the unit cell.

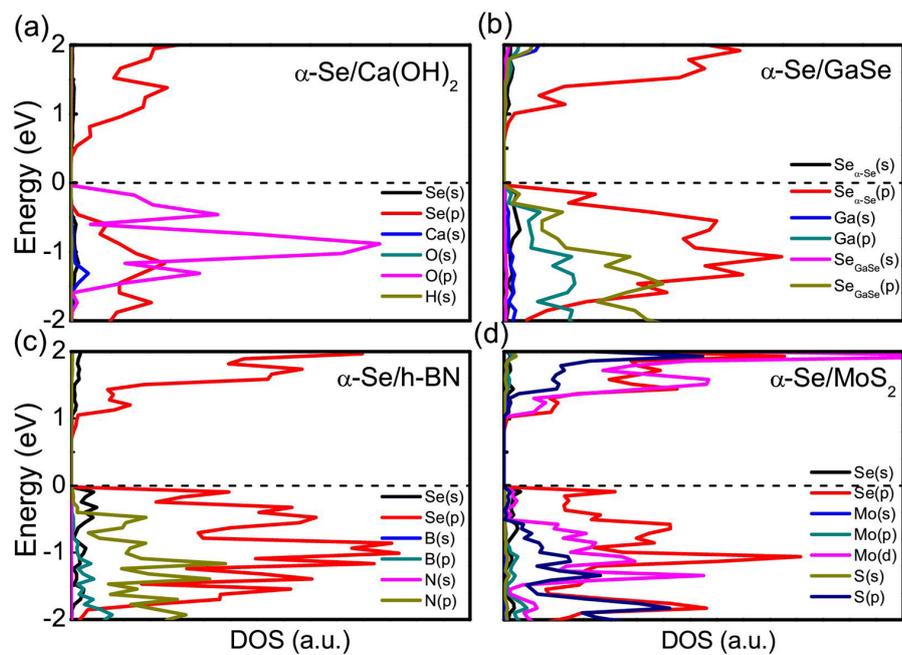


Figure S 8: (Color online). (a)-(d) The projected density of states (PDOS) of α -Se/ $\text{Ca}(\text{OH})_2$, α -Se/GaSe, α -Se/h-BN and α -Se/ MoS_2 VDWHs, respectively.

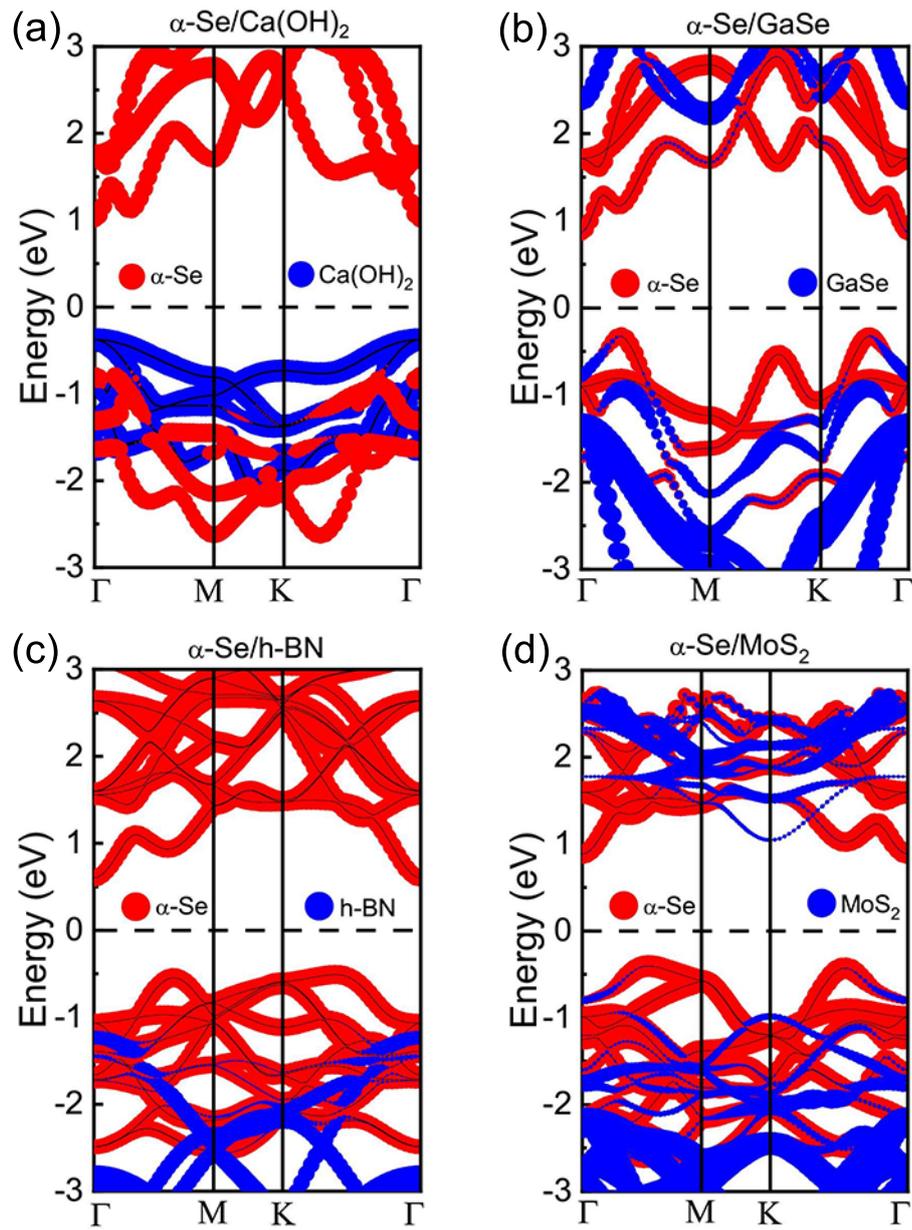


Figure S 9: (Color online). (a)-(d) The projected band structures of (a) α -Se/ $\text{Ca}(\text{OH})_2$, (c) α -Se/GaSe, (e) α -Se/h-BN and (g) α -Se/ MoS_2 VDWHs. The partial charge densities of the VBM and CBM for (b) α -Se/ $\text{Ca}(\text{OH})_2$, (d) α -Se/GaSe, (f) α -Se/h-BN and (h) α -Se/ MoS_2 VDWHs obtained by HSE06 functional, respectively.

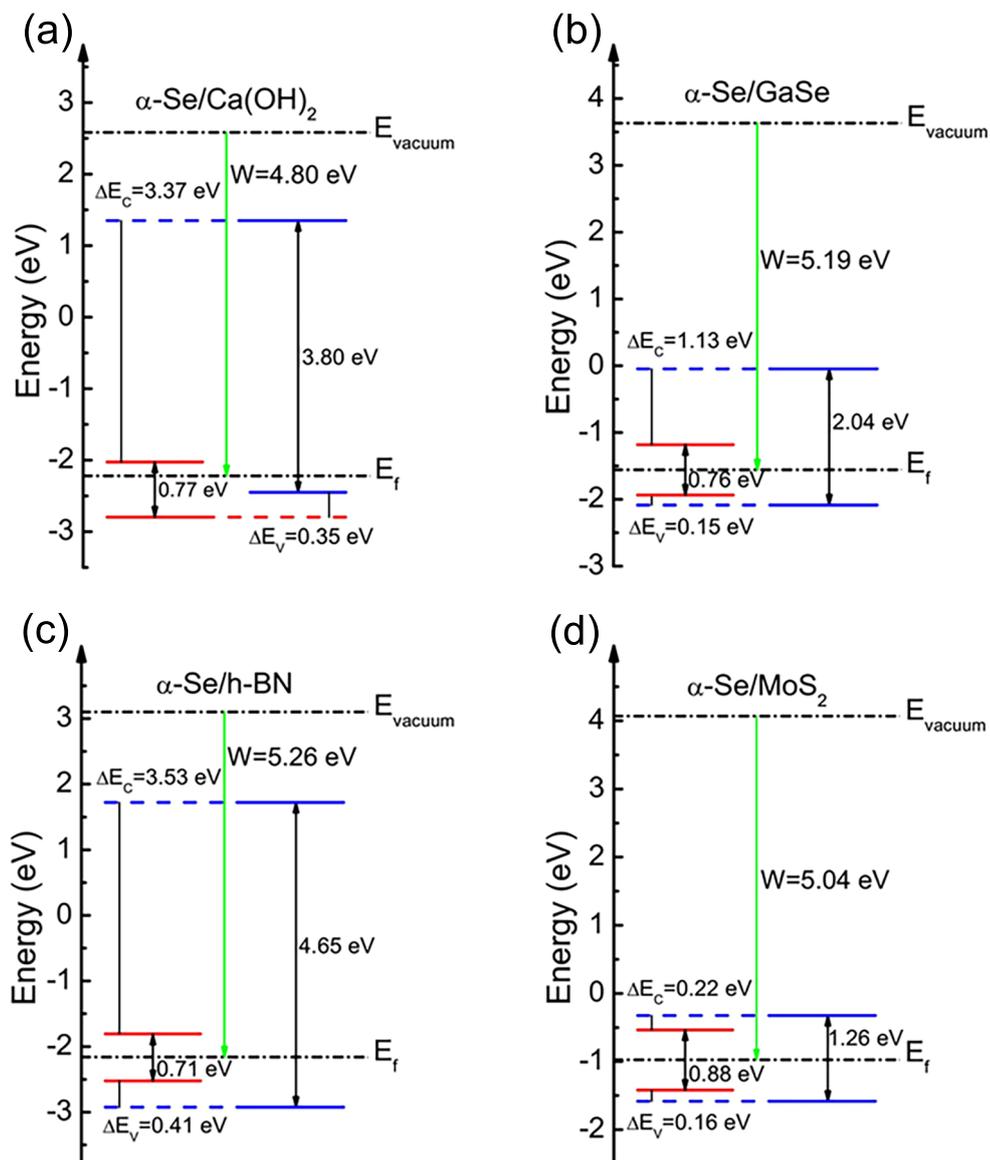


Figure S 10: (Color online). (a)-(d) The band alignment of α -Se/ $\text{Ca}(\text{OH})_2$, α -Se/GaSe, α -Se/h-BN and α -Se/ MoS_2 VDWHs, respectively.

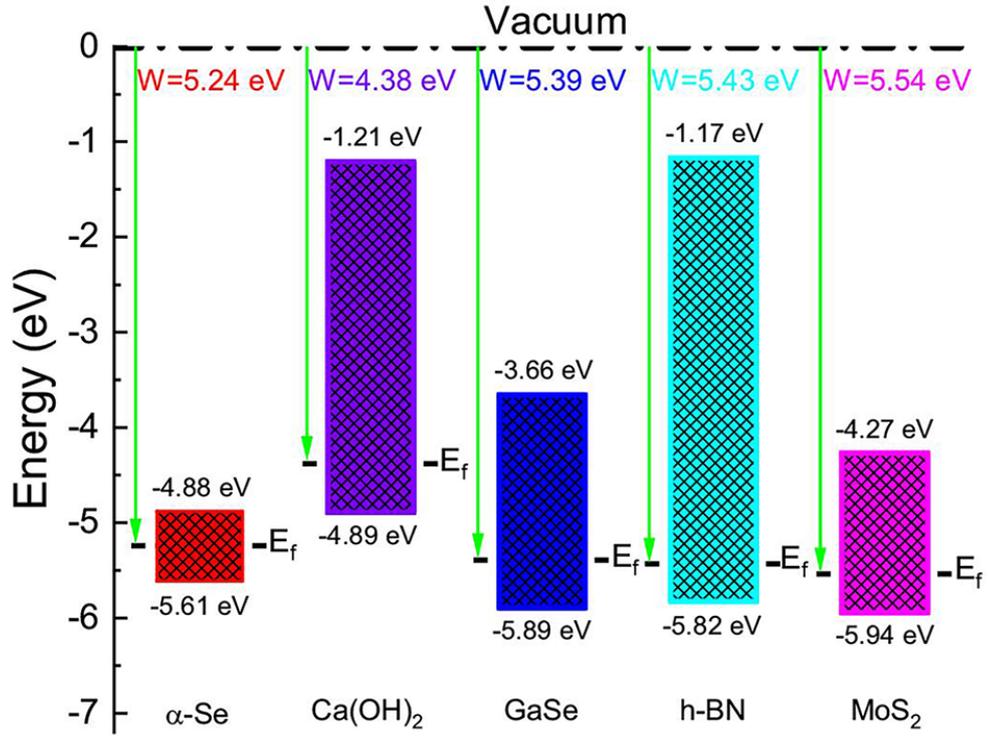


Figure S 11: (Color online). (a)-(e) The band-edge position of α -Se, Ca(OH)_2 , GaSe, h-BN and MoS_2 monolayers, respectively.

Table S II: The calculated effective mass for electrons and holes of α -Se/ Ca(OH)_2 , α -Se/GaSe, α -Se/h-BN and α -Se/ MoS_2 VDWHs along the x and y directions.

VDWH	$m_e^x (m_0)$	$m_e^y (m_0)$	$m_h^x (m_0)$	$m_h^y (m_0)$
α -Se/ Ca(OH)_2	0.13	0.11	3.57	2.27
α -Se/GaSe	0.14	0.12	0.66	1.25
α -Se/h-BN	0.11	0.10	0.47	1.49
α -Se/ MoS_2	0.13	0.14	1.42	0.49

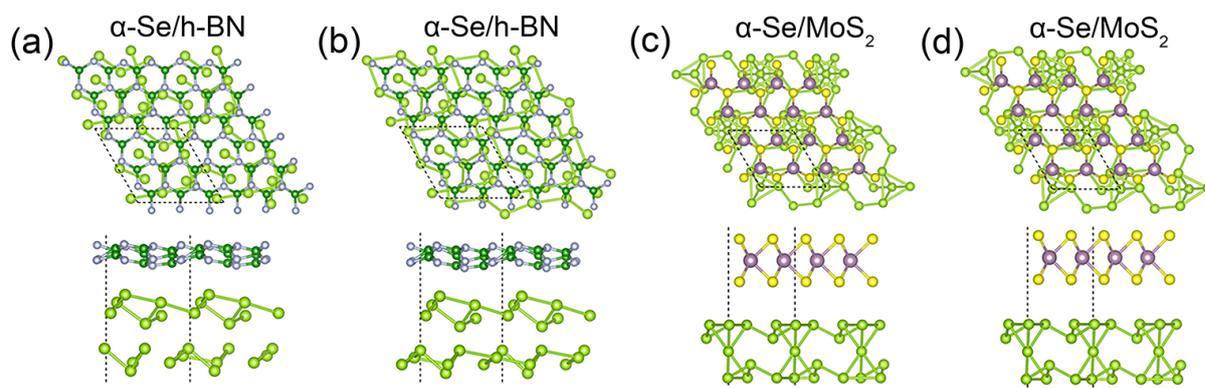


Figure S 12: (Color online). The structures of α -Se/h-BN VDWH when the compressive strain is (a) -9% and (b) -10%, respectively. The structures of α -Se/MoS₂ VDWH when the compressive strain is (c) -8% and (d) -10%, respectively.

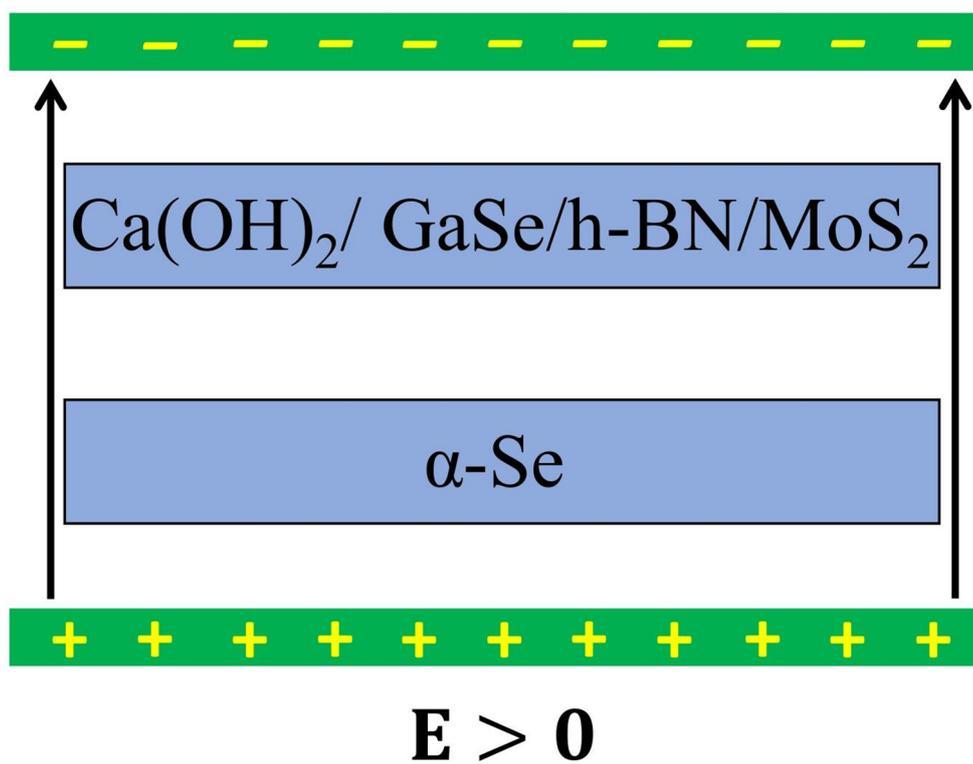


Figure S 13: (Color online). Schematic diagram of the positive electric field perpendicular to the interface of the four α -Se-based VDWHs.

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